

REPETITIVE AVALANCHE AND dv/dt RATED HEXFET® TRANSISTOR

IRHM7360 IRHM8360 N CHANNEL MEGA RAD HARD

400Volt, 0.22Ω, MEGA RAD HARD HEXFET

International Rectifier's RAD HARD technology HEXFETs demonstrate excellent threshold voltage stability and breakdown voltage stability at total radiation doses as high as 1×10^6 Rads(Si). Under **identical** pre- and post-irradiation test conditions, International Rectifier's RAD HARD HEXFETs retain **identical** electrical specifications up to 1×10^5 Rads(Si) total dose. No compensation in gate drive circuitry is required. These devices are also capable of surviving transient ionization pulses as high as 1×10^{12} Rads(Si)/Sec, and return to normal operation within a few microseconds. Since the RAD HARD process utilizes International Rectifier's patented HEXFET technology, the user can expect the highest quality and reliability in the industry.

RAD HARD HEXFET transistors also feature all of the well-established advantages of MOSFETs, such as voltage control, very fast switching, ease of paralleling and temperature stability of the electrical parameters. They are well-suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers and high-energy pulse circuits in space and weapons environments.

Product Summary

Part Number	BV _{DSS}	R _{DS(on)}	I _D
IRHM7360	400V	0.22Ω	22A
IRHM8360	400V	0.22Ω	22A

Features:

- Radiation Hardened up to 1×10^6 Rads (Si)
- Single Event Burnout (SEB) Hardened
- Single Event Gate Rupture (SEGR) Hardened
- Gamma Dot (Flash X-Ray) Hardened
- Neutron Tolerant
- Identical Pre- and Post-Electrical Test Conditions
- Repetitive Avalanche Rating
- Dynamic dv/dt Rating
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Electrically Isolated
- Ceramic Eyelets

Absolute Maximum Ratings ①


Pre-Irradiation

	Parameter	IRHM7230, IRHM8230	Units
I _D @ V _{GS} = 12V, T _C = 25°C	Continuous Drain Current	22	A
I _D @ V _{GS} = 12V, T _C = 100°C	Continuous Drain Current	14	
I _{DM}	Pulsed Drain Current ②	88	
P _D @ T _C = 25°C	Max. Power Dissipation	250	W
	Linear Derating Factor	2.0	W/°C
V _{GS}	Gate-to-Source Voltage	±20	V
EAS	Single Pulse Avalanche Energy ③	500	mJ
I _{AR}	Avalanche Current ②	22	A
EAR	Repetitive Avalanche Energy②	25	mJ
dv/dt	Peak Diode Recovery dv/dt ④	4.0	V/ns
T _J	Operating Junction	-55 to 150	°C
T _{STG}	Storage Temperature Range		
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)	
	Weight	9.3 (typical)	g

Electrical Characteristics @ T_j = 25°C (Unless Otherwise Specified) ①

	Parameter	Min	Typ	Max	Units	Test Conditions
BVDSS	Drain-to-Source Breakdown Voltage	400	—	—	V	V _{GS} = 0V, I _D = 1.0mA
ΔBVDSS/ΔT _J	Temperature Coefficient of Breakdown Voltage	—	0.45	—	V/°C	Reference to 25°C, I _D = 1.0mA
RDS(on)	Static Drain-to-Source On-State Resistance	—	—	0.22	Ω	V _{GS} = 12V, I _D = 14A ⑤
		—	—	0.25		V _{GS} = 12V, I _D = 22A
VGS(th)	Gate Threshold Voltage	2.0	—	4.0	V	V _{DS} = V _{GS} , I _D = 1.0mA
gfs	Forward Transconductance	6.0	—	—	S (r)	V _{DS} > 15V, I _{DS} = 14A ⑤
IDSS	Zero Gate Voltage Drain Current	—	—	50	μA	V _{DS} = 0.8 x Max Rating, V _{GS} = 0V
		—	—	250		V _{DS} = 0.8 x Max Rating V _{GS} = 0V, T _J = 125°C
IGSS	Gate-to-Source Leakage Forward	—	—	100	nA	V _{GS} = 20V
IGSS	Gate-to-Source Leakage Reverse	—	—	-100		V _{GS} = -20V
Qg	Total Gate Charge	—	—	210	nC	V _{GS} = 12V, I _D = 22A
Qgs	Gate-to-Source Charge	—	—	45		V _{DS} = Max Rating x 0.5
Qgd	Gate-to-Drain ('Miller') Charge	—	—	120		
td(on)	Turn-On Delay Time	—	—	33	ns	V _{DD} = 200V, I _D = 22A, R _G = 2.35Ω
t _r	Rise Time	—	—	59		
td(off)	Turn-Off Delay Time	—	—	140		
t _f	Fall Time	—	—	75		
L _D	Internal Drain Inductance	—	8.7	—	nH	Measured from drain lead, 6mm (0.25 in) from package to center of die.
L _S	Internal Source Inductance	—	8.7	—		Measured from source lead, 6mm (0.25 in) from package to source bonding pad.
Ciss	Input Capacitance	—	5600	—	pF	V _{GS} = 0V, V _{DS} = 25V f = 1.0MHz
Coss	Output Capacitance	—	990	—		
C _{rss}	Reverse Transfer Capacitance	—	380	—		

Source-Drain Diode Ratings and Characteristics ①

	Parameter	Min	Typ	Max	Units	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	22	A	Modified MOSFET symbol showing the integral reverse p-n junction rectifier. 
I _{SM}	Pulse Source Current (Body Diode) ②	—	—	88		
V _{SD}	Diode Forward Voltage	—	—	1.8	V	T _j = 25°C, I _S = 22A, V _{GS} = 0V ⑤
t _{rr}	Reverse Recovery Time	—	—	1000	ns	T _j = 25°C, I _F = 22A, di/dt ≤ 100A/μs V _{DD} ≤ 50V ⑤
Q _{RR}	Reverse Recovery Charge	—	—	11	μC	
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L _S + L _D .				

Thermal Resistance

	Parameter	Min	Typ	Max	Units	Test Conditions
R _{thJC}	Junction-to-Case	—	—	0.5	°C/W	Typical socket mount
R _{thCS}	Case-to-Sink	—	0.21	—		
R _{thJA}	Junction-to-Ambient	—	—	48		

Radiation Performance of Rad Hard HEXFETs

International Rectifier Radiation Hardened HEXFETs are tested to verify their hardness capability. The hardness assurance program at International Rectifier comprises three radiation environments.

Every manufacturing lot is tested in a low dose rate (total dose) environment per MIL-STD-750, test method 1019 condition A. International Rectifier has imposed a standard gate condition of 12 volts per note 6 and a V_{DS} bias condition equal to 80% of the device rated voltage per note 7. Pre- and post- irradiation limits of the devices irradiated to 1×10^5 Rads (Si) are identical and are presented in Table 1, column 1, IRHM7360. Post-irradiation limits of the devices irradiated to 1×10^6 Rads (Si) are presented in

Table 1, column 2, IRHM8360. The values in Table 1 will be met for either of the two low dose rate test circuits that are used. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

High dose rate testing may be done on a special request basis using a dose rate up to 1×10^{12} Rads (Si)/Sec (See Table 2).

International Rectifier radiation hardened HEXFETs have been characterized in heavy ion Single Event Effects (SEE) environments. Single Event Effects characterization is shown in Table 3.

Table 1. Low Dose Rate ⑥ ⑦

Table 1. Low Dose Rate ⑥ ⑦		IRHM7360		IRHM8360		Units	Test Conditions ⑨
	Parameter	100K Rads (Si)		1000K Rads (Si)			
		Min	Max	Min	Max		
BV _{DSS}	Drain-to-Source Breakdown Voltage	400	—	400	—	V	V _{GS} = 0V, I _D = 1.0mA
V _{GS(th)}	Gate Threshold Voltage ⑤	2.0	4.0	1.25	4.5		V _{GS} = V _{DS} , I _D = 1.0mA
I _{GSS}	Gate-to-Source Leakage Forward	—	100	—	100	nA	V _{GS} = 20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	-100	—	-100		V _{GS} = -20 V
I _{DSS}	Zero Gate Voltage Drain Current	—	50	—	100	μA	V _{DS} =0.8 x Max Rating, V _{GS} =0V
R _{DS(on)1}	Static Drain-to-Source ⑤ On-State Resistance One	—	0.22	—	0.31	Ω	V _{GS} = 12V, I _D = 14A
V _{SD}	Diode Forward Voltage ⑤	—	1.8	—	1.8	V	T _C = 25°C, I _S = 22A, V _{GS} = 0V

Table 2. High Dose Rate ⑧

	Parameter	10 ¹¹ Rads (Si)/sec			10 ¹² Rads (Si)/sec			Units	Test Conditions
		Min	Typ	Max	Min	Typ	Max		
V_{DSS}	Drain-to-Source Voltage	—	—	320	—	—	320	V	Applied drain-to-source voltage during gamma-dot
I_{pp}		—	6.4	—	—	6.4	—	A	Peak radiation induced photo-current
di/dt		—	—	16	—	—	2.3	A/ μ sec	Rate of rise of photo-current
L_1		20	—	—	137	—	—	μH	Circuit inductance required to limit di/dt

Table 3. Single Event Effects

Ion	LET (Si) (MeV/mg/cm ²)	Fluence (ions/cm ²)	Range (μm)	$V_{DS} \text{ Bias}$ (V)	$V_{GS} \text{ Bias}$ (V)
Ni	28	1×10^5	~41	275	-5

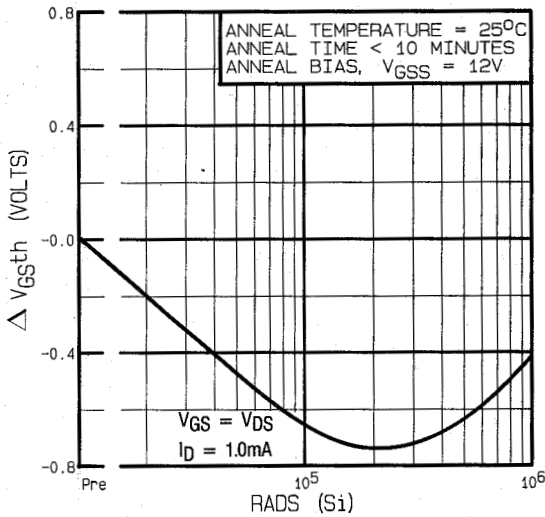


Fig 1. Typical Response of Gate Threshold Voltage Vs. Total Dose Exposure

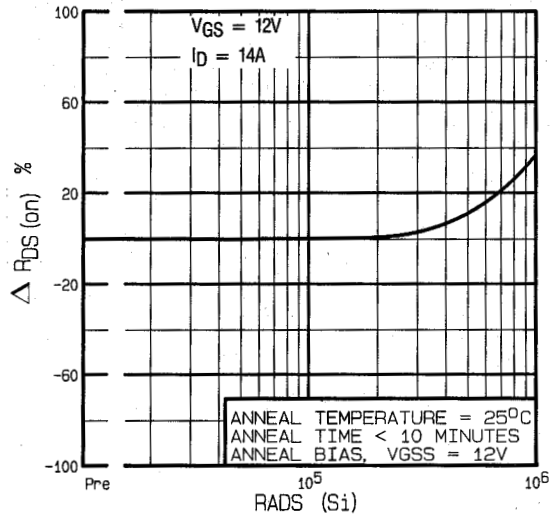


Fig 2. Typical Response of On-State Resistance Vs. Total Dose Exposure

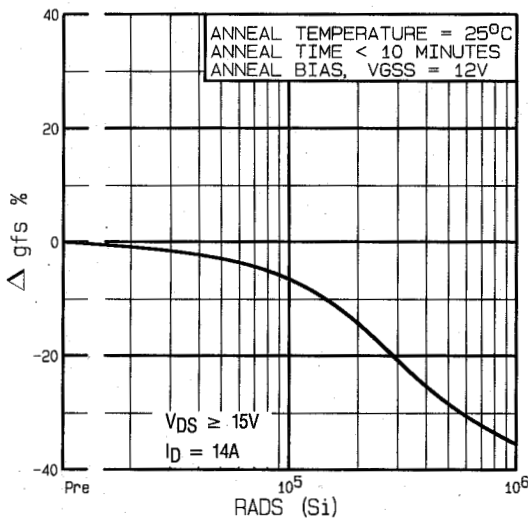


Fig 3. Typical Response of Transconductance Vs. Total Dose Exposure

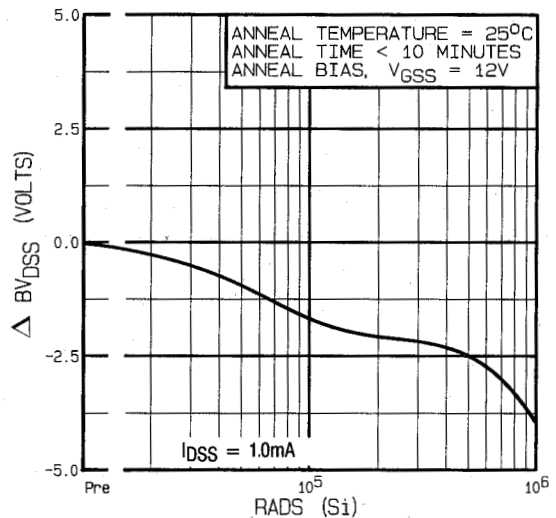


Fig 4. Typical Response of Drain to Source Breakdown Vs. Total Dose Exposure

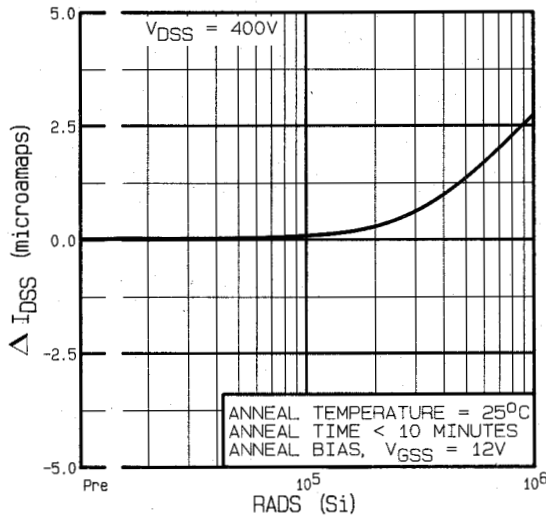


Fig 5. Typical Zero Gate Voltage Drain Current Vs. Total Dose Exposure

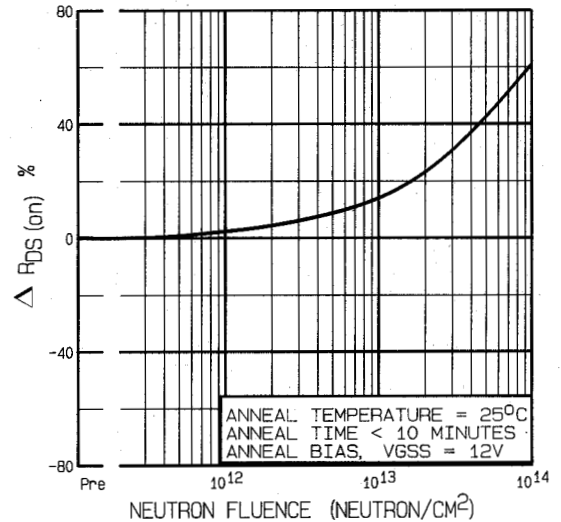


Fig 6. Typical On-State Resistance Vs. Neutron Fluence Level

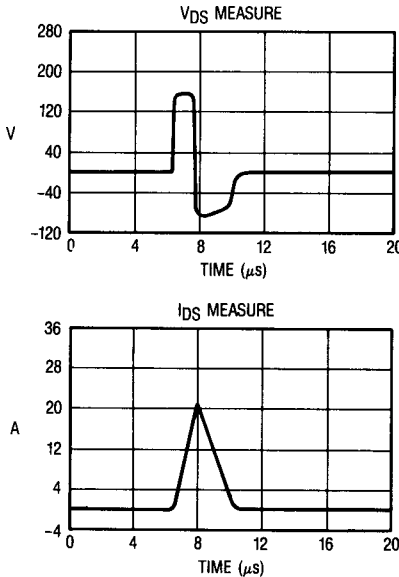


Fig 7. Typical Transient Response of Rad Hard HEXFET During 1×10^{12} Rad (Si)/Sec Exposure

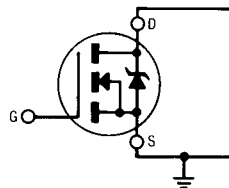


Fig 8a. Gate Stress of V_{GSS} Equals 12 Volts During Radiation

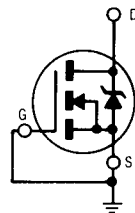


Fig 8b. V_{DS} Stress Equals 80% of B_{VDS} During Radiation

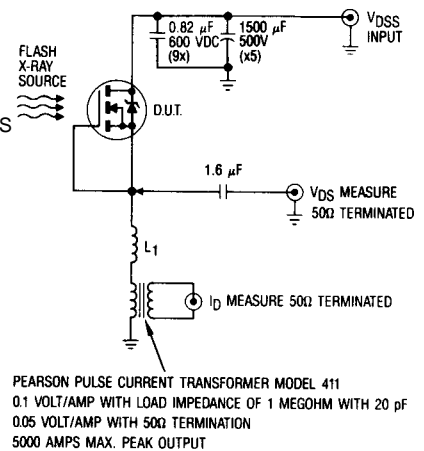


Fig 9. High Dose Rate (Gamma Dot) Test Circuit

Note: Bias Conditions during radiation: $V_{GS} = 12\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$

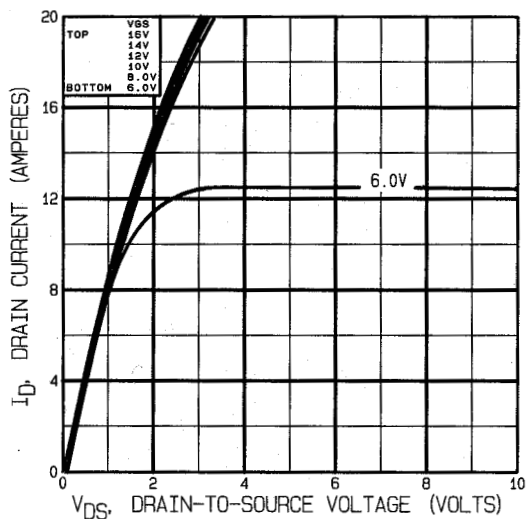


Fig 10. Typical Output Characteristics
Pre-Irradiation

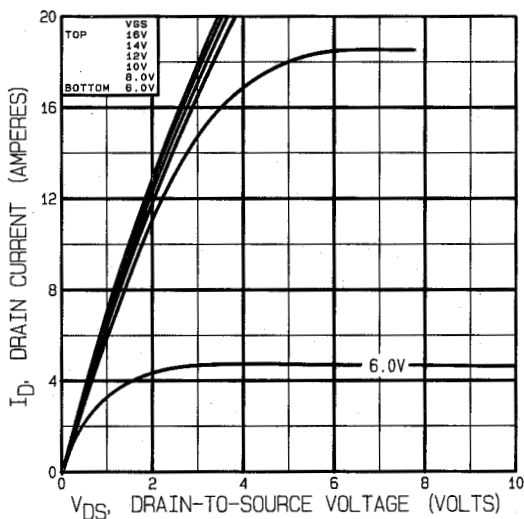


Fig 11. Typical Output Characteristics
Post-Irradiation 100K Rads (Si)

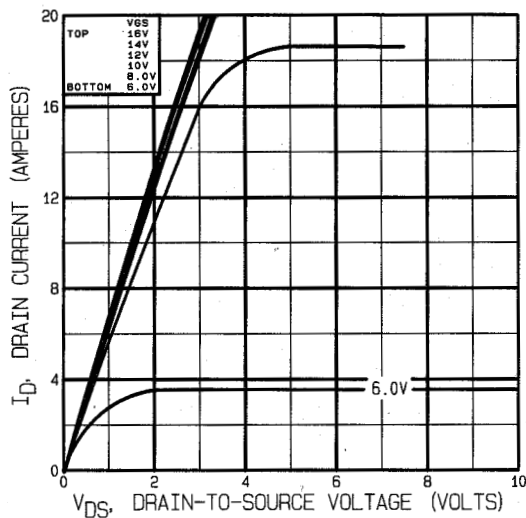


Fig 12. Typical Output Characteristics
Post-Irradiation 300K Rads (Si)

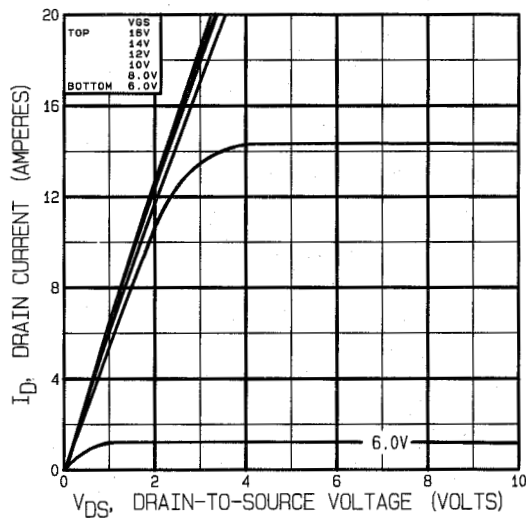


Fig 13. Typical Output Characteristics
Post-Irradiation 1 Mega Rads (Si)

Note: Bias Conditions during radiation: $V_{GS} = 0$ Vdc, $V_{DS} = 320$ Vdc

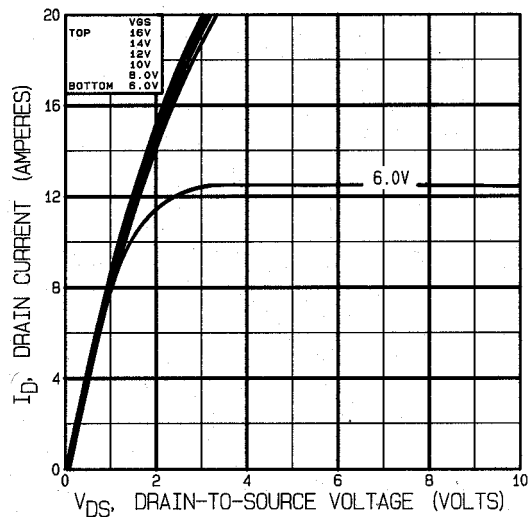


Fig 14. Typical Output Characteristics
Pre-Irradiation

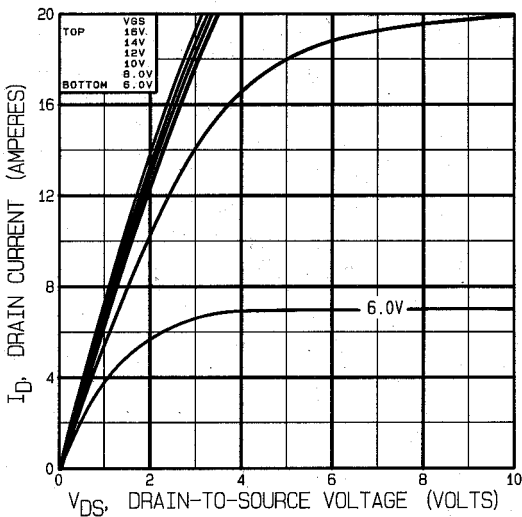


Fig 15. Typical Output Characteristics
Post-Irradiation 100K Rads (Si)

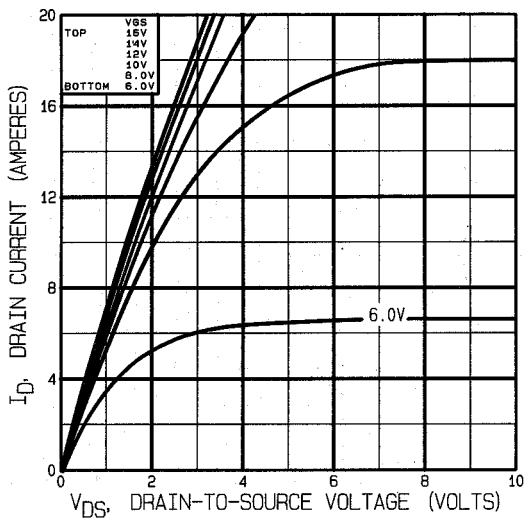


Fig 16. Typical Output Characteristics
Post-Irradiation 300K Rads (Si)

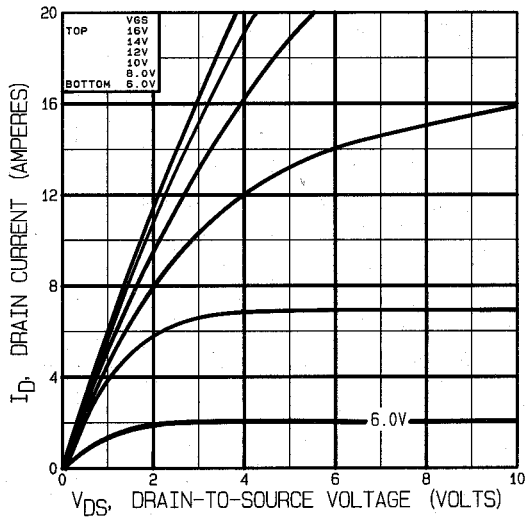


Fig 17. Typical Output Characteristics
Post-Irradiation 1 Mega Rads (Si)

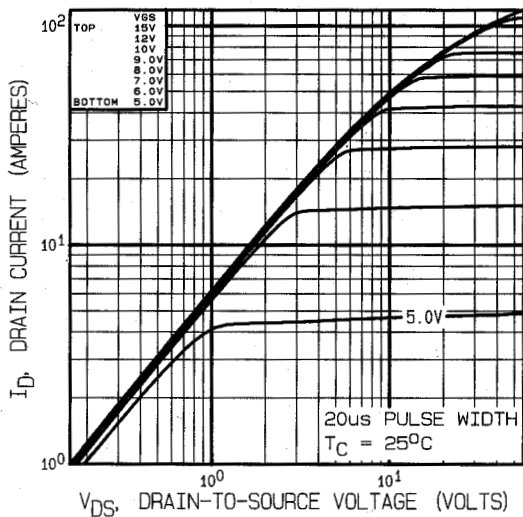


Fig 18. Typical Output Characteristics

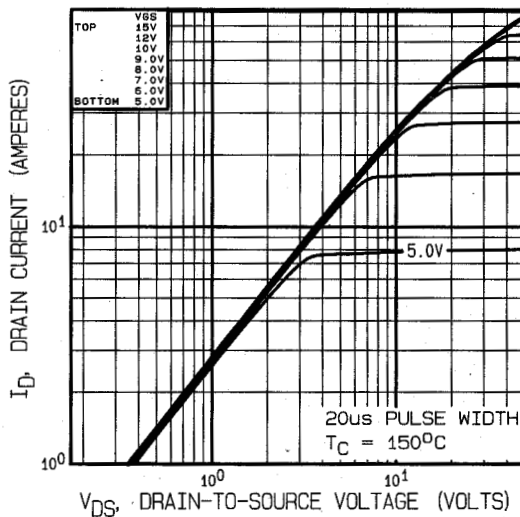


Fig 19. Typical Output Characteristics

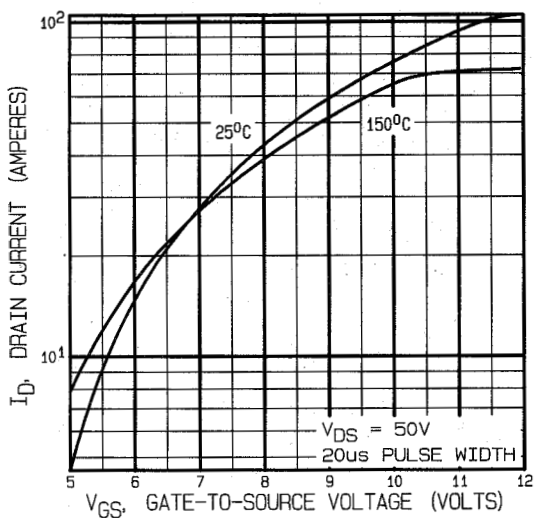


Fig 20. Typical Transfer Characteristics

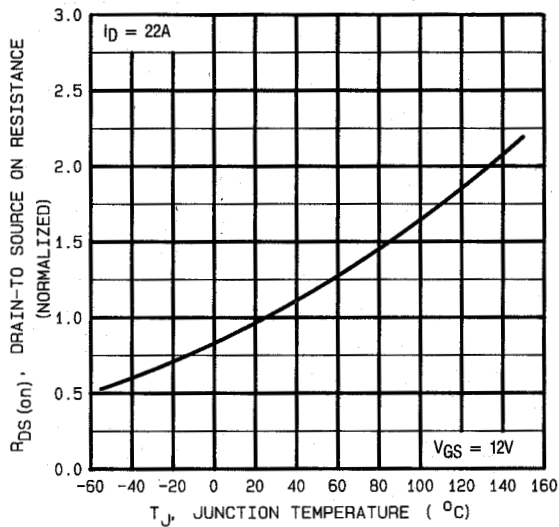
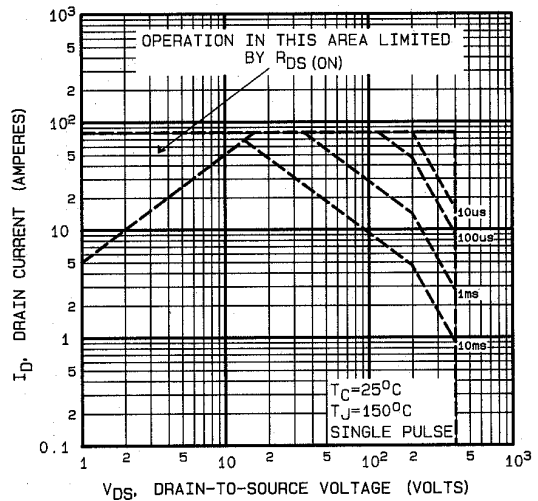
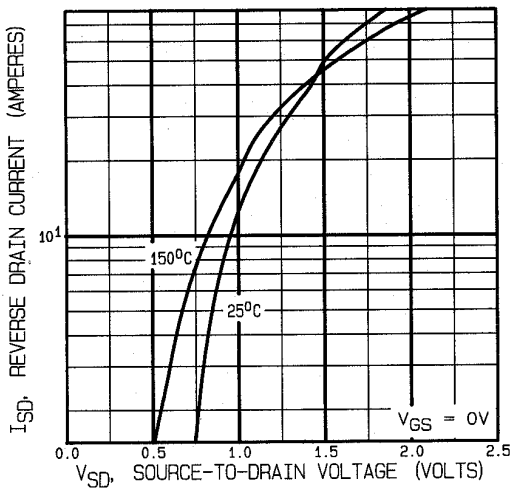
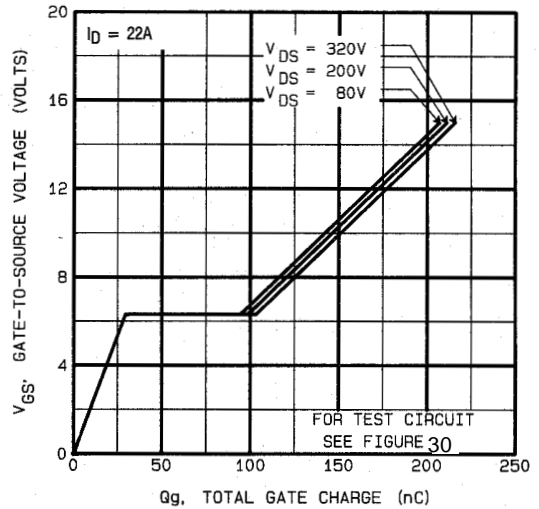
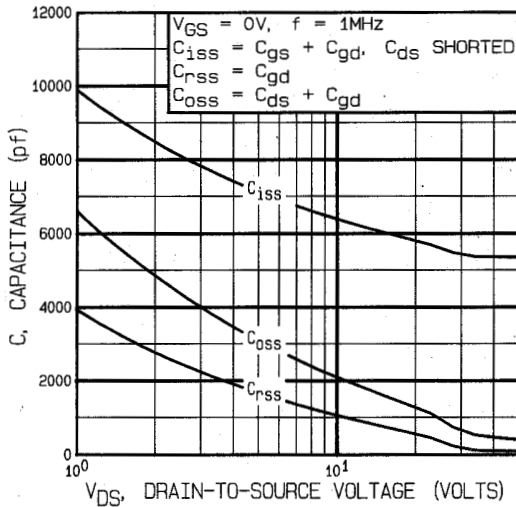


Fig 21. Normalized On-Resistance Vs. Temperature



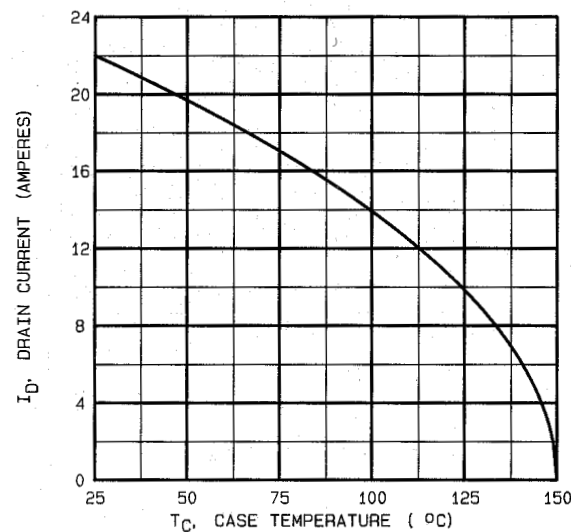


Fig 26. Maximum Drain Current Vs. Case Temperature

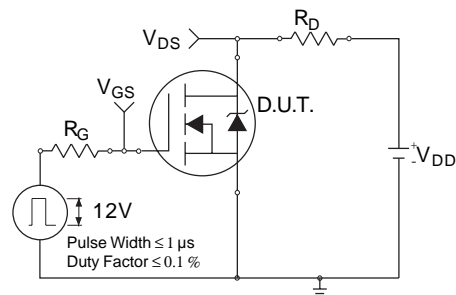


Fig 27a. Switching Time Test Circuit

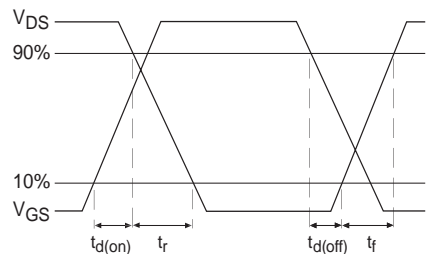


Fig 27b. Switching Time Waveforms

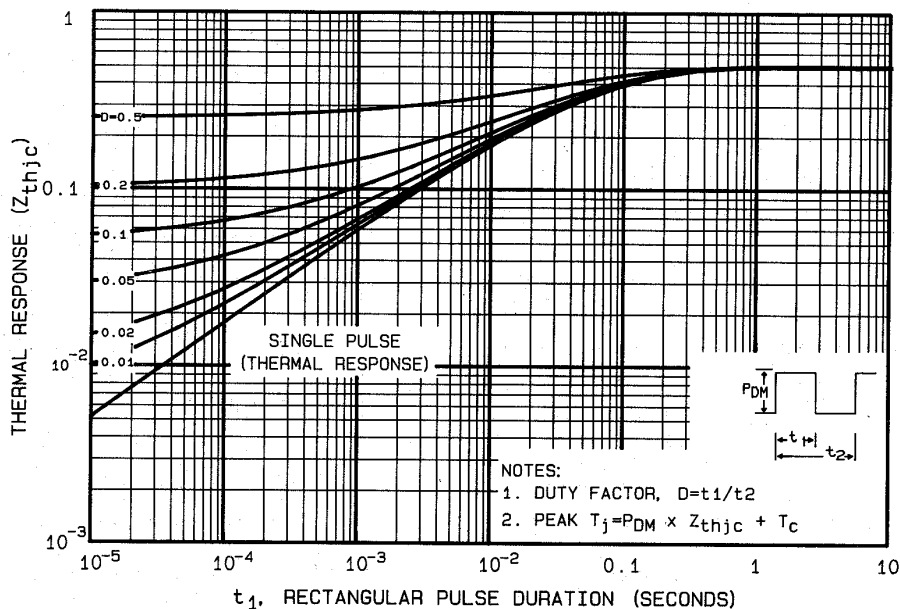


Fig 28. Maximum Effective Transient Thermal Impedance, Junction-to-Case

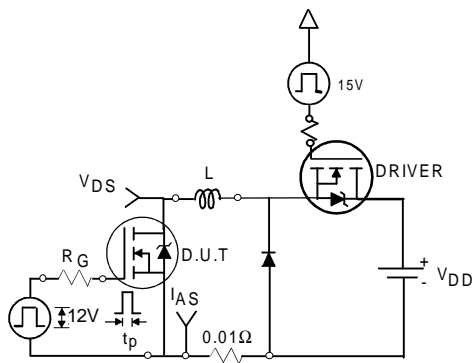


Fig 29a. Unclamped Inductive Test Circuit

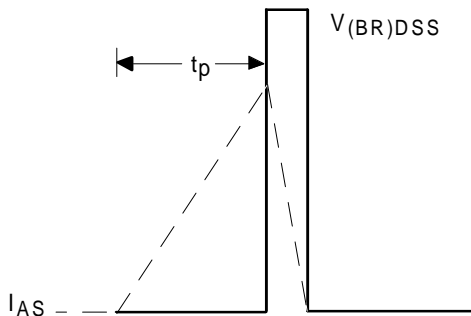


Fig 29b. Unclamped Inductive Waveforms

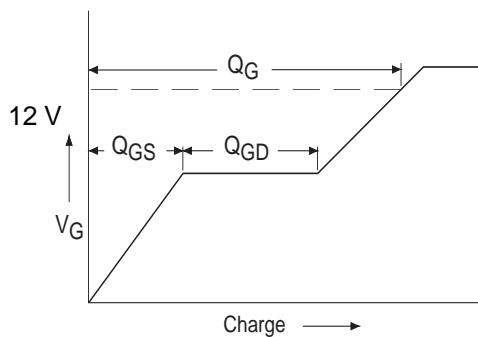


Fig30a. Basic Gate Charge Waveform

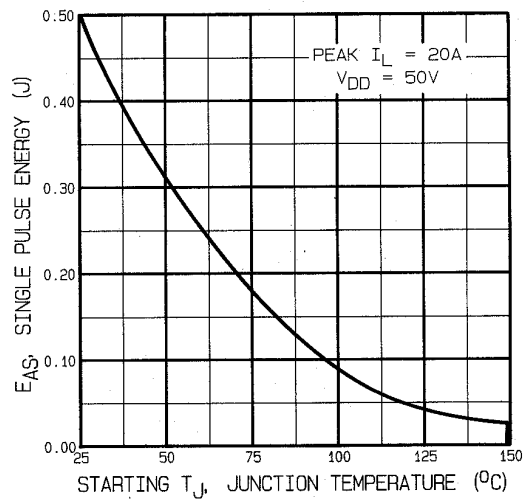


Fig 29c. Maximum Avalanche Energy Vs. Drain Current

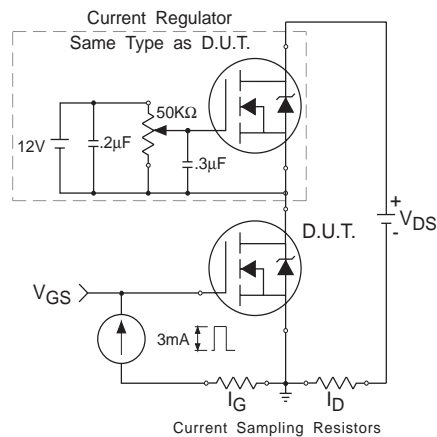


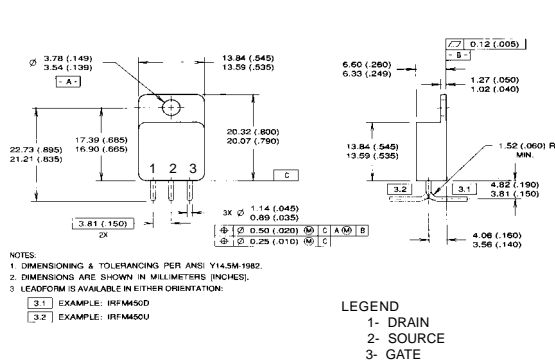
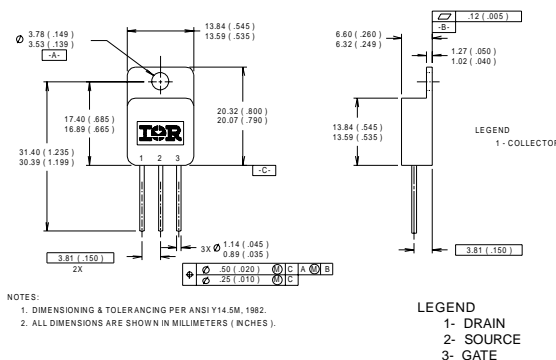
Fig 30b. Gate Charge Test Circuit

IRHM7360, IRHM8360 Devices

Pre-Irradiation

- ① See Figures 18 through 30 for pre-radiation curves
- ② Repetitive Rating; Pulse width limited by maximum junction temperature. Refer to current HEXFET reliability report.
- ③ $V_{DD} = 25V$, Starting $T_J = 25^\circ C$, Peak $I_L = 22A$, $R_G = 2.35\Omega$
- ④ $I_{SD} \leq 22A$, $di/dt \leq 120A/\mu s$, $V_{DD} \leq BV_{DSS}$, $T_J \leq 150^\circ C$
Suggested $R_G = 2.35\Omega$
- ⑤ Pulse width $\leq 300 \mu s$; Duty Cycle $\leq 2\%$
- ⑥ **Total Dose Irradiation with V_{GS} Bias.**
12 volt V_{GS} applied and $V_{DS} = 0$ during irradiation per MIL-STD-750, method 1019, condition A.
- ⑦ **Total Dose Irradiation with V_{DS} Bias.**
 $V_{DS} = 0.8$ rated BV_{DSS} (pre-irradiation) applied and $V_{GS} = 0$ during irradiation per MIL-STD-750, method 1019, condition A.
- ⑧ This test is performed using a flash x-ray source operated in the e-beam mode (energy ~ 2.5 MeV), 30 nsec pulse.
- ⑨ All Pre-Irradiation and Post-Irradiation test conditions are **identical** to facilitate direct comparison for circuit applications.

Case Outline and Dimensions — TO-254AA



Conforms to JEDEC Outline TO-254AA
Dimensions in Millimeters and (Inches)

CAUTION

BERYLLIA WARNING PER MIL-PRF-19500

Package containing beryllia shall not be ground, sandblasted, machined, or have other operations performed on them which will produce beryllia or beryllium dust. Furthermore, beryllium oxide packages shall not be placed in acids that will produce fumes containing beryllium.

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IR Rectifier

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